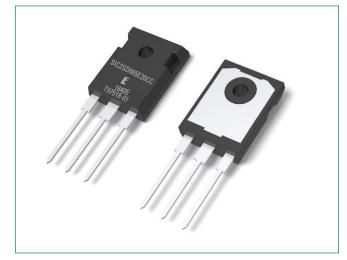
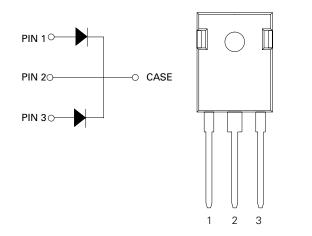
LSIC2SD065E20CCA 650 V, 20 A SiC Schottky Barrier Diode

HF RoHS 🗭



Circuit Diagram TO-247-3L



Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- AEC-Q101 qualified
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C. maximum operating junction temperature

Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies

Environmental

- Littelfuse "RoHS" logo = RoHS RoHS conform
- Littelfuse "HF" logo = **HF** Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating

Solar inverters

diodes

• Industrial motor drives

• Excellent surge capability

temperature-independent

switching behavior

• Dramatically reduced

compared to Si bipolar

switching losses

• Extremely fast,

• EV charging stations

Maximum Ratings

Characteristics	Symbol	Conditions	Value	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	-	650	V	
DC Blocking Voltage	V _R	T _J = 25 °C	650	V	
Continuous Forward Current (Per Leg/Component)	١ _F	T _c = 25 °C	27 / 54	Α	
		T _c = 147 °C	10 / 20		
Non-Repetitive Forward Surge Current (Per Leg)	I _{FSM}	$T_{c} = 25 \text{ °C}, t_{p} = 10 \text{ ms}, \text{ Half sine pulse}$	50	А	
Power Dissipation	D	$T_c = 25 \text{ °C}$	100 / 200	w	
(Per Leg/Component)	P _{Tot}	$T_c = 110 \text{ °C}$	43 / 86	vv	
Operating Junction Temperature	TJ	-	-55 to 175	°C	
Storage Temperature	T _{stg}	-	-55 to 150	°C	
Soldering Temperature	T _{sold}	-	260	°C	

Electrical Characteristics	(T = 25 °C unless of	herwise specified)
	1 - 25 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	nerwise speenieu/

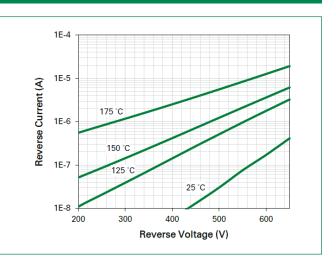
Characteristics Symbol	Symbol	Conditions	Value			11
	Symbol		Min.	Тур.	Max.	Unit
Forward Voltage V _F	I _F = 10 A, T _J = 25 °C	-	1.5	1.8		
	V _F	V _F I _F = 10 A, T _J = 175 °C	-	1.85	-	V
Reverse Current I _R	V _R = 650 V, T _J = 25 °C	-	<1	50		
	R	V _R = 650 V, T _J = 175 °C	-	25	-	μA
Total Capacitance C	$V_{R} = 1 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	470	-		
	V _R = 200 V, f = 1 MHz	-	60	-	pF	
		$V_{_{ m R}} = 400 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	43	-	
Total Capacitive Charge	Q _c	$V_{R} = 400 \text{ V}, \text{ Q}_{c} = \int C(V) dV$	-	30	-	nC

Thermal Characteristics				
Characteristics	Symbol	Value	Unit	
Thermal Resistance (Per Leg/Component)	R _{ejc}	1.50 / 0.75	°C/W	

10 9 T_J = -55 °C T_J = 25°C -8 T_J = 125 °C -7 T_J = 150 °C T_J = 175 °C 6 Current (A) 5 4 3 2 1 0 0 0.25 0.5 0.75 1 1.25 1.5 1.75 2 Voltage (V)

Figure 1: Typical Foward Characteristics

Figure 2: Typical Reverse Characteristics







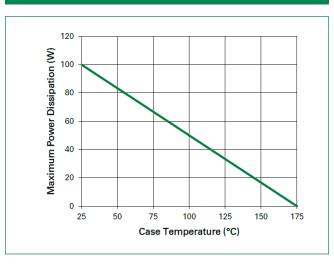


Figure 5: Capacitance vs. Reverse Voltage

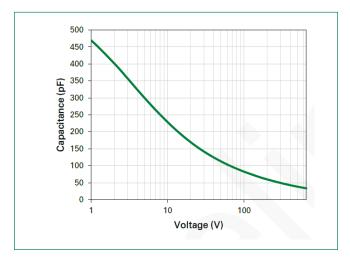


Figure 7: Stored Energy vs. Reverse Voltage

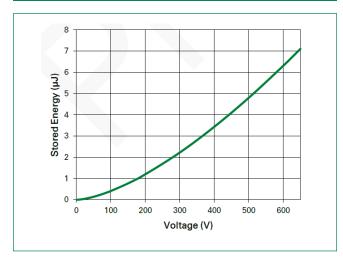


Figure 4: Current Derating

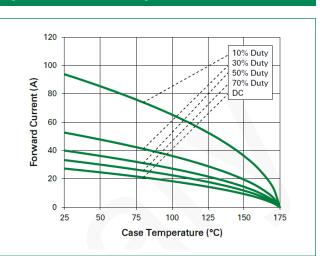


Figure 6: Capacitive Charge vs. Reverse Voltage

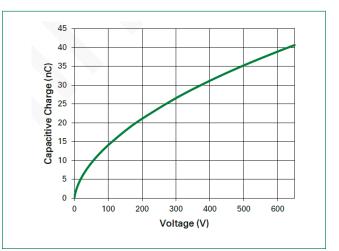
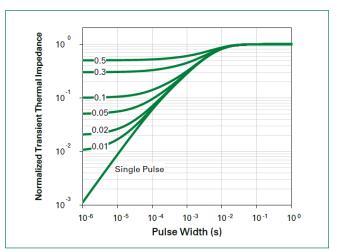
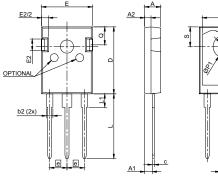


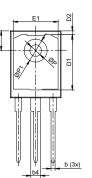
Figure 8: Transient Thermal Impedance



GEN2 SiC Schottky Diode LSIC2SD065E20CCA, 650 V, 20 A, TO-247-3L

Package Dimensions TO-247-3L





Recommended Hole Pattern Layout

 \oplus

Φ 5.44 5.44 UNIT: mm

R0.93 A O

Notes: 1. Dimensions are in millimeters 2. Dimension D, E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These measured at the outermost extreme of plastic body. 3. Pt to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 0.154°

Notes

• • • •	Millimeters			
Symbol	Min	Nom	Мах	
А	4.80	5.03	5.20	
A1	2.25	2.38	2.54	
A2	1.85	1.98	2.11	
b	0.99	-	1.40	
b2	1.65	-	2.39	
b4	2.59	-	3.43	
С	0.38	0.64	0.89	
D	20.80	20.96	21.34	
D1	13.50	-	-	
D2	0.51	1.19	1.35	
е		5.44 BSC		
E	15.75	15.90	16.13	
E1	13.06	14.02	14.15	
E2	4.19	4.32	4.83	
L	19.81	20.19	20.57	
L1	3.81	4.19	4.45	
øP	3.55	3.61	3.66	
øP1	7.06	7.19	7.32	
٥	5.49	5.61	6.20	
S	6.05	6.17	6.30	

Part Numbering and Marking System

SIC

065

Е

20

СС

YΥ

Х

WW

2 SD



- = SiC
- = Gen2
- = Schottky Diode
- = Voltage Rating (650 V)
- = T0-247-3L
- = Current Rating (20 A)
- = Common Cathode
- = Year
- = Week
- = Trace Code (Any Letter)

= Lot Number 777777-77

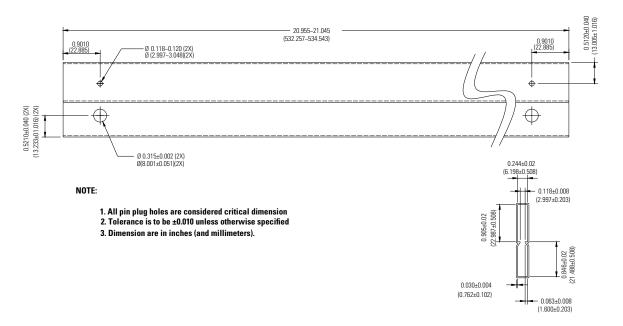
Packing Options

Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD065E20CCA	SIC2SD065E20CC	Tube (30pcs)	450



GEN2 SiC Schottky Diode LSIC2SD065E20CCA, 650 V, 20 A, T0-247-3L

Packing Specification TO-247-3L



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